

Surface Mount Hyperabrupt Wide-Band Tuning Varactors

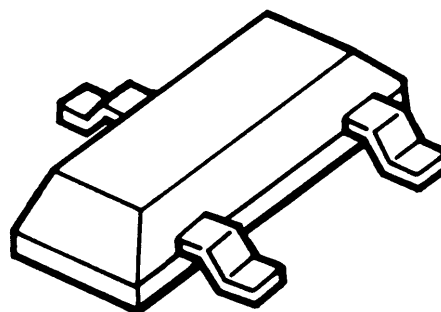
MA4ST079 thru 083

V3.00

Features

- Low Cost
- Very High Capacitance Ratio from 1 to 8 Volts
- Surface Mount Package
- High Quality Factor
- Useful for Battery Applications
- SPC Monitored Ion Implantation for Excellent C-V Repeatability
- Singles and Common Cathode Pairs
- Available in Tape and Reel

SOT-23

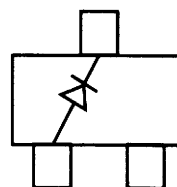


Description

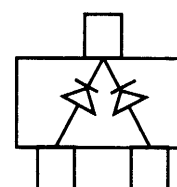
The MA4ST079 through MA4ST083 series of silicon hyperabrupt junction tuning varactors is produced with ion implantation and advanced epitaxial growth techniques. These diodes have thermal oxide passivation, and feature very high capacitance ratio and quality factor. They are well suited for use from the sub-HF through UHF frequency range. The standard capacitance tolerance is $\pm 10\%$, with tighter tolerances available. Capacitance matching at one or more bias voltages is also available.

Configurations

TOP VIEW



(SINGLE)



(COMMON CATHODE PAIR)

Applications

The MA4ST079 through MA4ST083 series of hyperabrupt junction tuning varactors is suggested for usage where a large frequency change is required with only a small change in tuning voltage.

This series is appropriate for usage in wide band voltage controlled oscillators and voltage controlled filters which require the largest rate of change of capacitance with voltage. The large change in capacitance from 1 to 8 volts makes them very attractive for battery operated or other systems with limited available control voltage.

The MA4ST079 through MA4ST083 family can be used in VCOs and VTFs from approximately 100 KHz through the UHF frequency band.

Specifications Subject to Change Without Notice.

M/A-COM, Inc.

North America: Tel. (800) 366-2266
Fax (800) 618-8883

■ Asia/Pacific: Tel. +81 3 3263 8761
Fax +81 3 3263 8769

■ Europe: Tel. +44 (1344) 869 595
Fax +44 (1344) 300 020

Electrical Specifications @ 25°CBreakdown Voltage @ $I_R = 10 \mu A$, $V_B = 12$ Volts MinimumReverse Leakage Current @ $V_R = 10$ Volts, $I_R = 100$ nA MaximumTemperature Coefficient of Capacitance @ $V_R = 8$ Volts, TCC = 400 ppm/°C Typical

Model Number	Minimum Total Capacitance (pF)	Total Capacitance (pF)		Maximum Total Capacitance (pF)	Maximum Total Capacitance (pF)	Typical Total Capacitance Ratio C_{T1}/C_{T8}	Typical Q
	f = 1 MHz $V_R = 1$ Volt	f = 1 MHz $V_R = 2.5$ Volts min. max.		f = 1 MHz $V_R = 4$ Volts	f = 1 MHz $V_R = 8$ Volts	f = 1 MHz $V_R = 1/ V_R=8$	f = 50 MHz $V_R = 4$ Volts
MA4ST079	87.4	48.7	59.5	27.3	11.8	9.1	80
MA4ST080	40.0	22.3	27.3	13.1	5.5	8.9	150
MA4ST081	16.2	9.1	11.1	5.2	2.4	8.5	300
MA4ST082	11.5	6.6	8.0	3.8	1.8	8.2	350
MA4ST083	7.9	4.5	5.5	2.6	1.3	7.8	450

Absolute Maximum Ratings @ 25°C

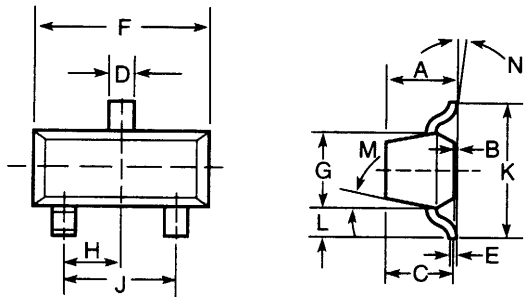
Parameter	Absolute Maximum
Reverse Voltage	12 Volts
Junction Temperature	-65°C to +125°C
Storage Temperature	-65°C to +125°C
Forward Current	50 mA
Power Dissipation	50 mW @ 25°C

Ordering Information

The part numbers shown are for single diodes. When ordering diodes in common cathode pairs add suffix "CK." For example, MA4ST079CK specifies model number MA4ST079 as a common cathode pair. To order parts on tape and reel add suffix T/R to the end of the part number. i.e. MA4ST079-T/R

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Case Style
SOT-23 (High Profile)



Package Capacitance = 0.15 pF typical
Package Inductance = 2 nH typical

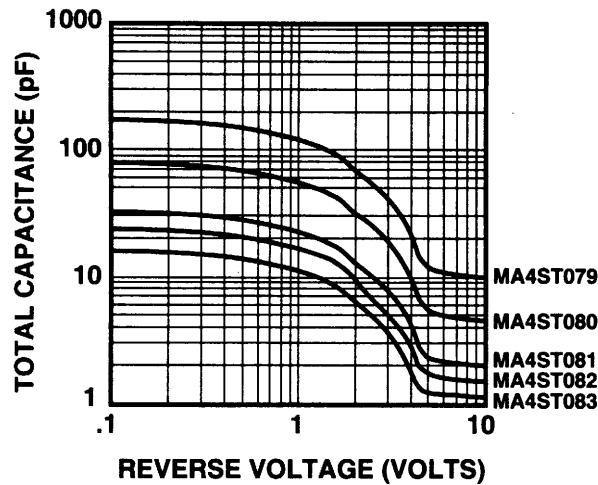
DIM.	INCHES		MILLIMETERS	
	MIN.	MAX.	MIN.	MAX.
A	—	0.048	—	1.22
B	—	0.008	—	0.20
C	—	0.040	—	1.00
D	0.013	0.020	0.35	0.50
E	0.003	0.006	0.08	0.15
F	0.110	0.119	2.80	3.00
G	0.047	0.056	1.20	1.40
H	0.037 typical		0.95 typical	
J	0.075 typical		1.90 typical	
K		0.103		2.60
L		0.024		0.60

DIM.	GRADIENT
M	10° max. ¹
N	2°...30°

Note:
1. Applicable on all sides

Typical Performance Curves

TOTAL CAPACITANCE vs REVERSE VOLTAGE



NOMINAL Q vs REVERSE VOLTAGE

